

20 V, 2 A P-channel Trench MOSFET Rev. 1 — 28 June 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

1.3 Applications

- Relay driver
- High-speed line driver

- Trench MOSFET technology
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

| Quick reference data | | | | | | |
|----------------------------------|--|---|--|--|---|---|
| Parameter | Conditions | | Min | Тур | Max | Unit |
| drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| gate-source voltage | | | -12 | - | 12 | V |
| drain current | V_{GS} = -4.5 V; T_j = 25 °C | <u>[1]</u> | - | - | -2 | А |
| aracteristics | | | | | | |
| drain-source on-state resistance | V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C | | - | 90 | 115 | mΩ |
| | drain-source voltage gate-source voltage drain current aracteristics drain-source on-state | $\begin{array}{c} \text{drain-source voltage} & T_j = 25 \ ^{\circ}\text{C} \\ \text{gate-source voltage} \\ \text{drain current} & V_{\text{GS}} = -4.5 \ \text{V}; \ \text{T}_j = 25 \ ^{\circ}\text{C} \\ \end{array}$ | drain-source voltage gate-source voltage $T_j = 25 \text{ °C}$ drain current $V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$ aracteristicsdrain-source on-state $V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$ | $\begin{array}{c} \mbox{drain-source voltage} & T_j = 25 \ ^{\circ}\ C & -12 \\ \mbox{gate-source voltage} & V_{GS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}\ C & 11 \\ \mbox{aracteristics} & & \\ \mbox{drain-source on-state} & V_{GS} = -4.5 \ V; \ I_D = -2 \ A; \ T_j = 25 \ ^{\circ}\ C & - \end{array}$ | drain-source voltage gate-source voltageT_j = 25 °C-drain current $V_{GS} = -4.5 V; T_j = 25 °C$ -12drain current $V_{GS} = -4.5 V; T_j = 25 °C$ -drain-source on-state $V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C$ - | $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

| Table 2. | Pinning | j information | | |
|----------|---------|---------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | | |
| 2 | D | drain | | |
| 3 | G | gate | | |
| 4 | S | source | | |
| 5 | D | drain | | Ś |
| 6 | D | drain | SOT363 (TSSOP6) | 017aaa094 |

3. Ordering information

| Table 3. Orde | ering information | | |
|---------------|-------------------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| PMG85XP | TSSOP6 | plastic surface-mounted package; 6 leads | SOT363 |

4. Marking

| Table 4. Marking codes | |
|------------------------|-----------------------------|
| Type number | Marking code ^[1] |
| PMG85XP | YA% |

[1] % = placeholder for manufacturing site code

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5. Limiting values

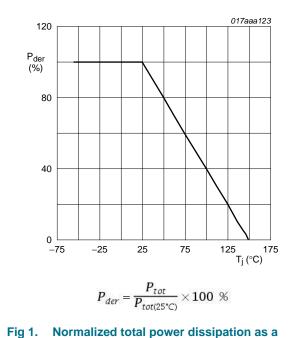
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

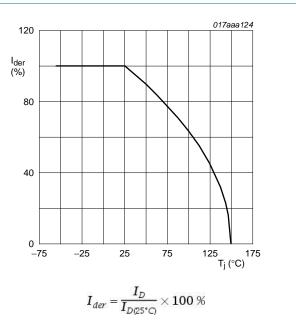
| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--|-------------------------|--|------------|-----|------|------|
| V _{DS} | drain-source voltage | $T_j = 25 \ ^{\circ}C$ | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _j = 25 °C | <u>[1]</u> | - | -2 | А |
| | | V _{GS} = -4.5 V; T _j = 100 °C | <u>[1]</u> | - | -1.3 | А |
| I _{DM} | peak drain current | $T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$ | | - | -8 | А |
| P _{tot} total power dissipation | total power dissipation | T _{amb} = 25 °C | [2] | - | 375 | mW |
| | | | [1] | - | 725 | mW |
| | | T _{sp} = 25 °C | | - | 2400 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drai | in diode | | | | | |
| ls | source current | T _{amb} = 25 °C | [1] | - | -0.7 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

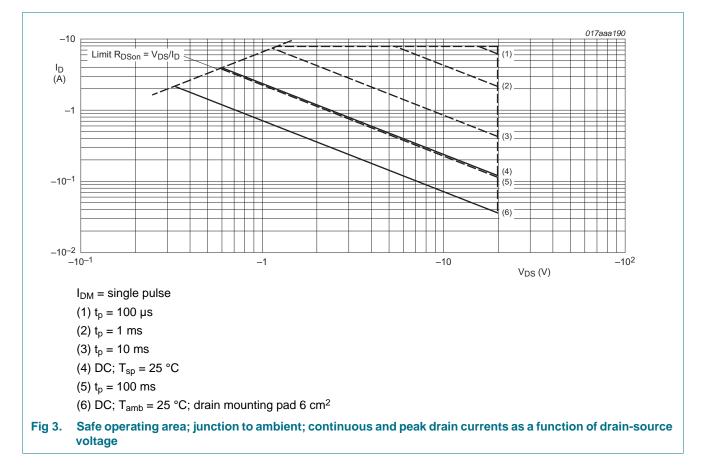


function of junction temperature





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6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|------------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance | in free air | <u>[1]</u> | - | 290 | 334 | K/W |
| | from junction to ambient | | [2] | - | 150 | 173 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 45 | 52 | K/W |

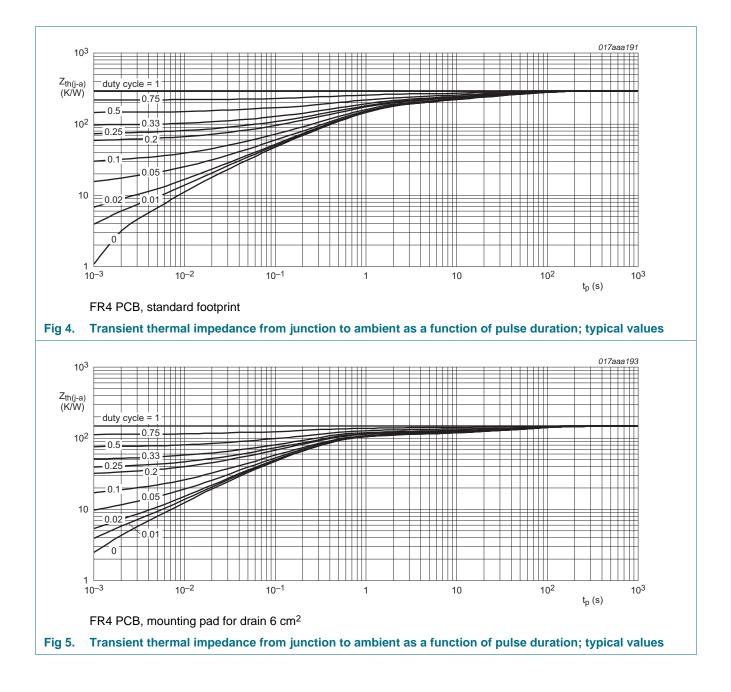
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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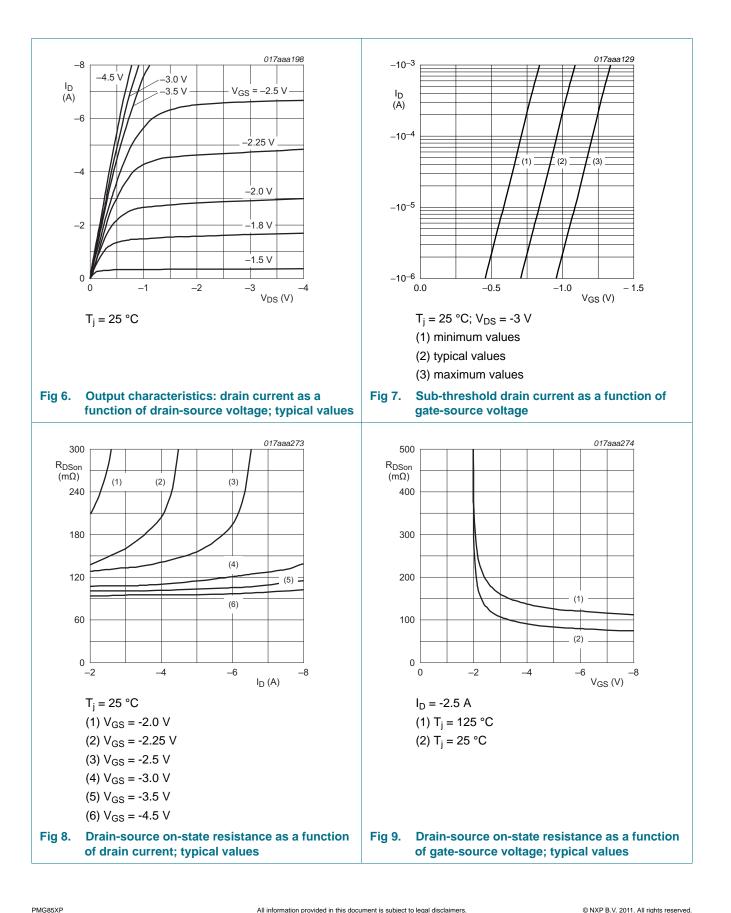


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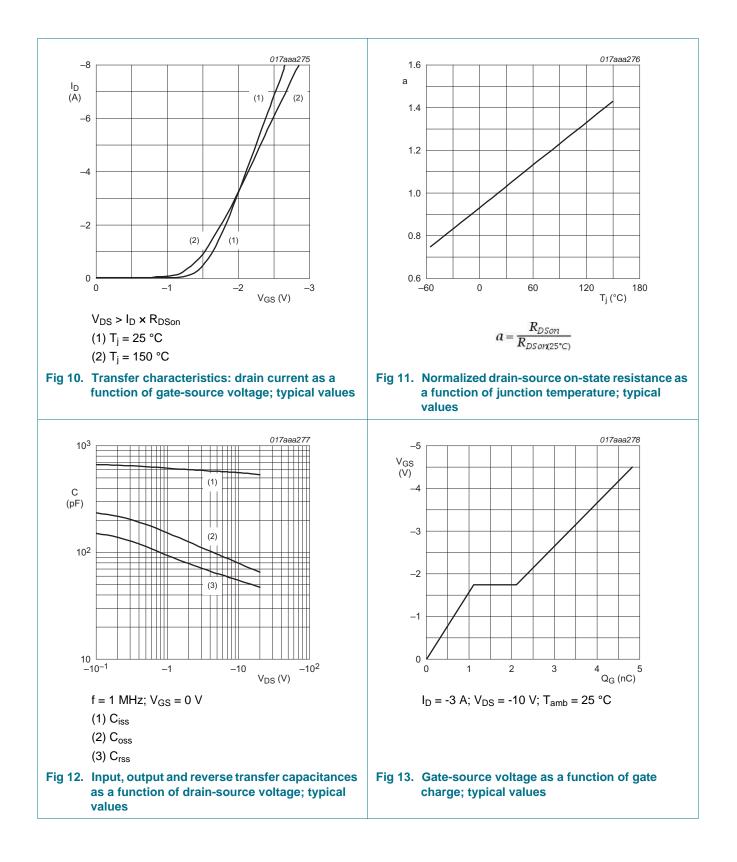
7. Characteristics

| Table 7. | Characteristics | | | | | |
|----------------------|-----------------------------------|--|-------|------|-------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C | -20 | - | - | V |
| V _{GSth} | gate-source threshold voltage | I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C | -0.65 | -0.9 | -1.15 | V |
| I _{DSS} | drain leakage current | V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C | - | - | -1 | μΑ |
| | | $V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | -15 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C | - | 90 | 115 | mΩ |
| | resistance | V_{GS} = -4.5 V; I _D = -2 A; T _j = 150 °C | - | 130 | 166 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -2 A; T_j = 25 °C | - | 125 | 160 | mΩ |
| 9 _{fs} | forward transconductance | $V_{DS} = -5 \text{ V}; \text{ I}_{D} = -2 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$ | - | 6.3 | - | S |
| Dynamic of | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $V_{DS} = -10 \text{ V}; \text{ I}_{D} = -1 \text{ A}; \text{ V}_{GS} = -4.5 \text{ V};$ | - | 4.8 | 7.2 | nC |
| Q _{GS} | gate-source charge | $T_j = 25 \ ^{\circ}C$ | - | 1.1 | - | nC |
| Q _{GD} | gate-drain charge | | - | 1 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = -10 \text{ V}; \text{ f} = 1 \text{ MHz}; \text{ V}_{GS} = 0 \text{ V};$ | - | 560 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 80 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 55 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ; | - | 13 | - | ns |
| t _r | rise time | $T_j = 25 \text{ °C}; I_D = -2.5 \text{ A}$ | - | 35 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 39 | - | ns |
| t _f | fall time | | - | 25 | - | ns |
| Source-dr | ain diode | | | | | |
| V _{SD} | source-drain voltage | I _S = -0.7 A; V _{GS} = 0 V; T _i = 25 °C | - | -0.7 | -1.2 | V |

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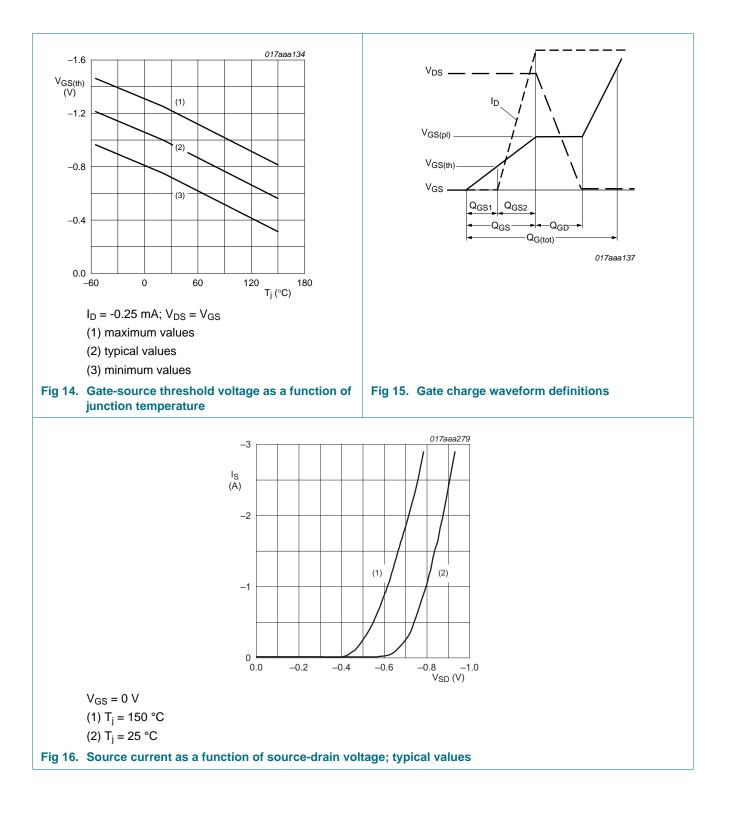
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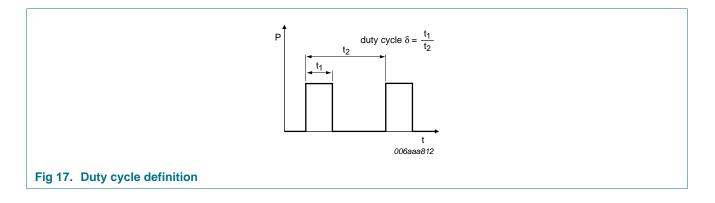
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8. Test information



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9. Package outline

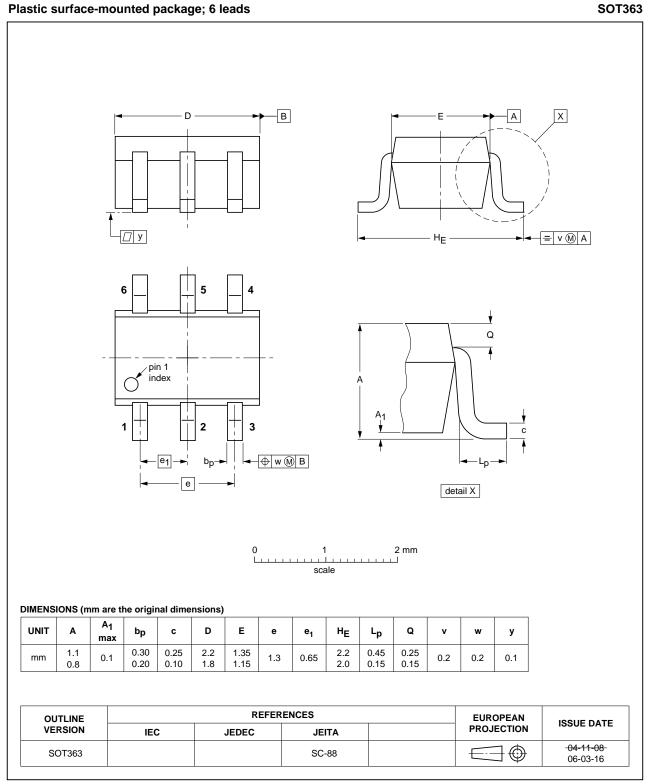
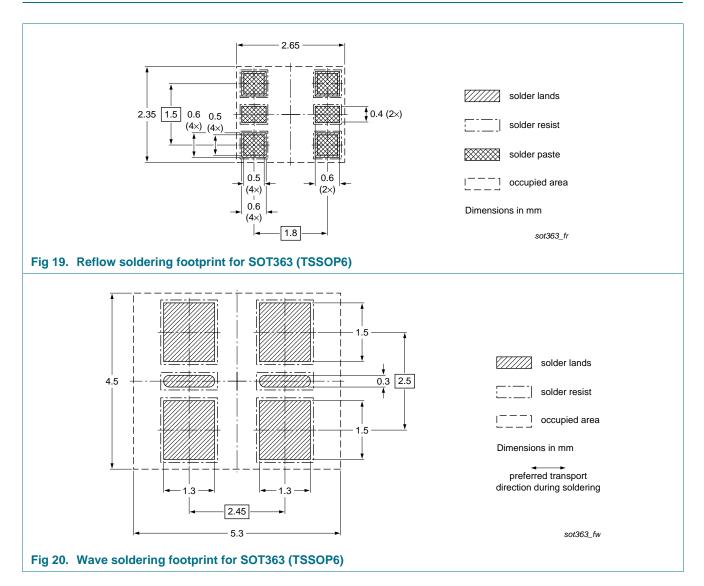


Fig 18. Package outline SOT363 (TSSOP6)

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10. Soldering



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11. Revision history

| Table 8. Revis | Revision history | | | | | | |
|----------------|------------------|--------------------|---------------|------------|--|--|--|
| Document ID | Release date | Data sheet status | Change notice | Supersedes | | | |
| PMG85XP v.N | 20110628 | Product data sheet | - | - | | | |

12. Legal information

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| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
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